

# Michael D Craven

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7819659/publications.pdf>

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10  
papers

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citations

933264

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1281743

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g-index

11  
all docs

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docs citations

11  
times ranked

536  
citing authors

#	ARTICLE	IF	CITATIONS
1	Reviewâ€”The Physics of Recombinations in III-Nitride Emitters. ECS Journal of Solid State Science and Technology, 2020, 9, 016021.	0.9	57
2	Compensation between radiative and Auger recombinations in III-nitrides: The scaling law of separated-wavefunction recombinations. Applied Physics Letters, 2019, 115, .	1.5	15
3	Many-Body Effects in Strongly Disordered III-Nitride Quantum Wells: Interplay Between Carrier Localization and Coulomb Interaction. Physical Review Applied, 2019, 12, .	1.5	22
4	Quantum Efficiency of III-Nitride Emitters: Evidence for Defect-Assisted Nonradiative Recombination and its Effect on the Green Gap. Physical Review Applied, 2019, 11, .	1.5	66
5	Thermal droop in high-quality InGaN LEDs. Applied Physics Letters, 2019, 115, .	1.5	25
6	All-optical measurements of carrier dynamics in bulk-GaN LEDs: Beyond the ABC approximation. Applied Physics Letters, 2017, 110, .	1.5	34
7	Field-assisted Shockley-Read-Hall recombinations in III-nitride quantum wells. Applied Physics Letters, 2017, 111, .	1.5	40
8	Carrier dynamics and Coulomb-enhanced capture in III-nitride quantum heterostructures. Applied Physics Letters, 2016, 109, .	1.5	30
9	Electrical properties of III-Nitride LEDs: Recombination-based injection model and theoretical limits to electrical efficiency and electroluminescent cooling. Applied Physics Letters, 2016, 109, .	1.5	46
10	Bulk GaN flip-chip violet light-emitting diodes with optimized efficiency for high-power operation. Applied Physics Letters, 2015, 106, .	1.5	197